



# ***AOS Semiconductor Product Reliability Report***

**AO4726/AO4726L, rev A**

**Plastic Encapsulated Device**

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This AOS product reliability report summarizes the qualification result for AO4726. Accelerated environmental tests are performed on a specific sample size, and then followed by electrical test at end point. Review of final electrical test result confirms that AO4726 passes AOS quality and reliability requirements. The released product will be categorized by the process family and be monitored on a quarterly basis for continuously improving the product quality.

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### I. Product Description:

The AO4726 uses advanced trench technology with a monolithically integrated Schottky diode to provide excellent  $R_{DS(ON)}$  and low gate charge. This device is suitable for use as a low side FET in SMPS, load switching and general purpose applications.

Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted				
Parameter	Symbol	10 sec	Steady state	Units
Drain-Source Voltage	$V_{DS}$	30		V
Gate-Source Voltage	$V_{GS}$	$\pm 12$		V
Continuous Drain Current	$T_A=25^\circ\text{C}$	18	13	A
	$T_A=70^\circ\text{C}$	$I_{DSM}$	10	
Pulsed Drain Current	$I_{DM}$	80		A
Avalanche Current	$I_{AR}$	42		A
Repetitive avalanche energy $L=0.3\text{mH}$	$E_{AR}$	265		mJ
Power Dissipation	$T_A=25^\circ\text{C}$	3.1	1.7	W
	$T_A=70^\circ\text{C}$	$P_{DSM}$	1.1	
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150		$^\circ\text{C}$

Thermal Characteristics					
Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient	$T \leq 10\text{s}$	$R_{\theta JA}$	32	40	$^\circ\text{C/W}$
Maximum Junction-to-Ambient	Steady-State		60	75	$^\circ\text{C/W}$
Maximum Junction-to-Lead	Steady-State	$R_{\theta JL}$	17	24	$^\circ\text{C/W}$

## II. Die / Package Information:

	<b>AO4726</b>	<b>AO4726L (Green Compound)</b>
<b>Process</b>	Standard sub-micron Low voltage N channel process	Standard sub-micron Low voltage N channel process
<b>Package Type</b>	8 leads SOIC	8 leads SOIC
<b>Lead Frame</b>	Cu, S/pad, Ag spot	Cu, S/pad, Ag spot
<b>Die Attach</b>	Ag epoxy	Ag epoxy
<b>Bond wire</b>	S: Cu 2mils, G: Au 1.3mils	S: Cu 2mils, G: Au 1.3mils
<b>Mold Material</b>	Epoxy resin with silica filler	Epoxy resin with silica filler
<b>Filler % (Spherical/Flake)</b>	90/10	100/0
<b>Flammability Rating</b>	UL-94 V-0	UL-94 V-0
<b>Backside Metallization</b>	Ti / Ni / Ag	Ti / Ni / Ag
<b>Moisture Level</b>	Up to Level 1 *	Up to Level 1*

**Note \*** based on info provided by assembler and mold compound supplier

## III. Result of Reliability Stress for AO4726 (Standard) & AO4726L (Green)

Test Item	Test Condition	Time Point	Lot Attribution	Total Sample size	Number of Failures
<b>Solder Reflow Precondition</b>	Standard: 1hr PCT+3 cycle reflow@260°C Green: 168hr 85°C /85%RH +3 cycles reflow@260°C	0hr	Standard: 83 lots Green: 29 lots	17380 pcs	0
<b>HTGB</b>	Temp = 150°C , Vgs=100% of Vgsmax	168 / 500 hrs  1000 hrs	3 lots  (Note A*)	246 pcs  77+5 pcs / lot	0
<b>HTRB</b>	Temp = 150°C , Vds=80% of Vdsmax	168 / 500 hrs  1000 hrs	3 lots  (Note A*)	246 pcs  77+5 pcs / lot	0
<b>HAST</b>	130 +/- 2°C , 85%RH, 33.3 psi, Vgs = 80% of Vgs max	100 hrs	Standard: 81 lots Green: 16 lots  (Note B**)	5335 pcs  50+5 pcs / lot	0
<b>Pressure Pot</b>	121°C , 29.7 psi , 100%RH	96 hrs	Standard: 83 lots Green: 20 lots  (Note B**)	5665 pcs  50+5 pcs / lot	0
<b>Temperature Cycle</b>	-65°C to 150°C , air to air	250 / 500 cycles	Standard: 87 lots Green: 29 lots  (Note B**)	6380 pcs  50+5 pcs / lot	0

### III. Result of Reliability Stress for AO4726 (Standard) & AO4726L (Green)

Continues

DPA	Internal Vision Cross-section X-ray	NA	5	5	0
			5	5	
			5	5	
CSAM		NA	5	5	0
Bond Integrity	Room Temp 150°C bake 150°C bake	0hr	40	40 wires	0
		250hr	40	40 wires	
		500hr	40	40 wires	
Solderability	245°C	5 sec	15	15 leads	0

**Note A:** The HTGB and HTRB reliability data presents total of available AO4726 and AO4726L burn-in data up to the published date.

**Note B:** The pressure pot, temperature cycle and HAST reliability data for AO4726 and AO4726L comes from the AOS generic package qualification data.

### IV. Reliability Evaluation

**FIT rate (per billion): 43**

**MTTF =2654 years**

In general, 500 hrs of HTGB, 150 deg C accelerated stress testing is equivalent to 15 years of lifetime at 55 deg C operating conditions (by applying the Arrhenius equation with an activation energy of 0.7eV and 60% of upper confidence level on the failure rate calculation). AOS reliability group also routinely monitors the product reliability up to 1000 hr at and performs the necessary failure analysis on the units failed for reliability test(s).

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size of the selected product (AO4726). Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

$$\text{Failure Rate} = \text{Chi}^2 \times 10^9 / [2 (N) (H) (Af)] = 1.83 \times 10^9 / [2 (3 \times 164) (168) (258)] = 43$$

$$\text{MTTF} = 10^9 / \text{FIT} = 2.32 \times 10^7 \text{hrs} = 2654 \text{ years}$$

**Chi<sup>2</sup>** = Chi Squared Distribution, determined by the number of failures and confidence interval

**N** = Total Number of units from HTRB and HTGB tests

**H** = Duration of HTRB/HTGB testing

**Af** = Acceleration Factor from Test to Use Conditions (Ea = 0.7eV and Tuse = 55°C)

$$\text{Acceleration Factor [Af]} = \text{Exp} [Ea / k (1/Tj u - 1/Tj s)]$$

**Acceleration Factor ratio list:**

	55 deg C	70 deg C	85 deg C	100 deg C	115 deg C	130 deg C	150 deg C
<b>Af</b>	<b>258</b>	<b>87</b>	<b>32</b>	<b>13</b>	<b>5.64</b>	<b>2.59</b>	<b>1</b>

**Tj s** = Stressed junction temperature in degree (Kelvin), K = C+273.16

**Tj u** =The use junction temperature in degree (Kelvin), K = C+273.16

**k** = Boltzmann's constant, 8.617164 X 10<sup>-5</sup>eV / K



## V. Quality Assurance Information

Acceptable Quality Level for outgoing inspection: **0.1%** for electrical and visual.

Guaranteed Outgoing Defect Rate: **< 25 ppm**

Quality Sample Plan: conform to **Mil-Std-105D**